

Next Generation OP07 Ultralow Offset Voltage Operational Amplifier

NP77

FEATURES

Outstanding gain linearity Ultrahigh gain, 5000 V/mV min Low V_{OS} over temperature, 55 μ V max Excellent TCV_{OS}, 0.3 μ V/°C max High PSRR, 3 μ V/V max Low power consumption, 60 mW max Fits OP07, 725,108A/308A, 741 sockets Available in die form

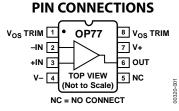
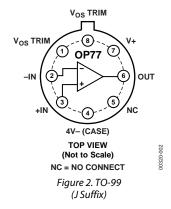


Figure 1. 8-Pin Hermetic DIP_Q-8 (Z Suffix)



GENERAL DESCRIPTION

The OP77 significantly advances the state-of-the-art in precision op amps. The outstanding gain of 10,000,000 or more for the OP77 is maintained over the full 10 V output range. This exceptional gain-linearity eliminates incorrectable system nonlinearities common in previous monolithic op amps and provides superior performance in high closed-loop gain applications. Low initial $V_{\rm OS}$ drift and rapid stabilization time, combined with only 50 mW of power consumption, are significant improvements over previous designs. These characteristics, plus the exceptional $TCV_{\rm OS}$ of 0.3 $\mu V/^{\circ}C$ maximum and the low $V_{\rm OS}$ of 25 μV maximum, eliminates the

need for V_{OS} adjustment and increases system accuracy over temperature.

A PSRR of 3 $\mu V/V$ (110 dB) and CMRR of 1.0 $\mu V/V$ maximum virtually eliminate errors caused by power supply drifts and common-mode signals. This combination of outstanding characteristics makes the OP77 ideally suited for high resolution instrumentation and other tight error budget systems.

OP77

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ELECTRICAL SPECIFICATIONS

@ $V_S = \pm 15$ V, $T_A = 25$ °C, unless otherwise noted.

Table 1.

				OP77E			OP77F		
Parameter	Symbol	Conditions	Min	Тур	Max	Min	Тур	Max	Unit
INPUT OFFSET VOLTAGE	Vos			10	25		20	60	μV
LONG-TERM STABILITY ¹	V _{os} /time			0.3			0.4		μV/Mo
INPUT OFFSET CURRENT	los			0.3	1.5		0.3	2.8	nA
INPUT BIAS CURRENT	I _B		-0.2	+1.2	+2.0	-0.2	+1.2	+2.8	nA
INPUT NOISE VOLTAGE ²	e _{np-p}	0.1 Hz to 10 Hz		0.35	0.6		0.38	0.65	μV_{p-p}
INPUT NOISE VOLTAGE DENSITY	e _n	f ₀ = 10 Hz		10.3	18.0		10.5	20.0	nV/√Hz
		$f_0 = 100 \text{ Hz}^2$		10.0	13.0		10.2	13.5	
		$f_0 = 1000 \text{ Hz}$		9.6	11.0		9.8	11.5	
INPUT NOISE CURRENT ²	i _{np-p}	0.1 Hz to 10 Hz		14	30		15	35	pA _{p-p}
INPUT NOISE CURRENT DENSITY	in	$f_0 = 10 \text{ Hz}$		0.32	0.80		0.35	0.90	pA√Hz
		$f_0 = 100 \text{ Hz}^2$		0.14	0.23		0.15	0.27	
		$f_0 = 1000 \text{ Hz}$		0.12	0.17		0.13	0.18	
INPUT RESISTANCE									
Differential Mode ³	R _{IN}		26	45		18.5	45		ΜΩ
Common Mode	RINCM			200			200		GΩ
INPUT VOLTAGE RANGE	IVR		±13	±14		±13	±14		V
COMMON-MODE REJECTION RATIO	CMRR	$V_{CM} = \pm 13 \text{ V}$		0.1	1.0		0.1	1.6	μV/V
POWER SUPPLY REJECTION RATIO	PSRR	$V_S = \pm 3 \text{ V to } \pm 18 \text{ V}$		0.7	3.0		0.7	3.0	μV/V
LARGE-SIGNAL VOLTAGE GAIN	A _{vo}	$R_L \ge 2 k\Omega$	5000	12,000		2000	6000		V/mV
		$V_0 = \pm 10 \text{ V}$							
OUTPUT VOLTAGE SWING	Vo	$R_L \ge 10 \ k\Omega$	±13.5	±14.0		±13.5	±14.0		V
		$R_L \geq 2 \; k\Omega$	±12.5	±13.0		±12.5	±13.0		
		$R_L \geq 1 \ k\Omega$	±12.0	±12.5		±12.0	±12.5		
SLEW RATE ²	SR	$R_L \ge 2 \ k\Omega$	0.1	0.3		0.1	0.3		V/µs
CLOSED-LOOP BANDWIDTH ²	BW	A _{VCL} + 1	0.4	0.6		0.4	0.6		MHz
OPEN-LOOP OUTPUT RESISTANCE	Ro			60			60		Ω
POWER CONSUMPTION	P _d	$V_S = \pm 15 \text{ V, no load}$		50	60		50	60	mW
		$V_s = \pm 3 \text{ V, no load}$		3.5	4.5		3.5	4.5	
OFFSET ADJUSTMENT RANGE		Rp = 20 kn		±3			±3		mV

 $^{^1}$ Long-term input offset voltage stability refers to the averaged trend line of V_{OS} vs. time over extended periods after the first 30 days of operation. Excluding the initial hour of operation, changes in V_{OS} during the first 30 operating days are typically 2.5 μ V. 2 Sample tested.

³ Guaranteed by design.

OP77

@ $V_S = \pm 15$ V, -25° C $\leq T_A \leq +85^{\circ}$ C for OP77FJ and OP77E/OP77F, unless otherwise noted.

Table 2.

				OP77E			OP77F		
Parameter	Symbol	Conditions	Min	Тур	Max	Min	Тур	Max	Unit
INPUT OFFSET VOLTAGE	Vos			10	45		20	100	μV
AVERAGE INPUT OFFSET VOLTAGE DRIFT ¹	TCVos			0.1	0.3		0.2	0.6	μV/°C
INPUT OFFSET CURRENT	los			0.5	2.2		0.5	4.5	nA
AVERAGE INPUT OFFSET CURRENT DRIFT ²	TClos			1.5	4.0		1.5	85	pA/°C
INPUT BIAS CURRENT	I _B		-0.2	+2.4	+4.0	-0.2	+2.4	+6.0	nA
AVERAGE INPUT BIAS CURRENT DRIFT ²	TCI _B			8	40		15	60	pA/°C
INPUT VOLTAGE RANGE	IVR		±13.0	±13.5		±13.0	±13.5		V
COMMON-MODE REJECTION RATIO	CMRR	$V_{CM} = \pm 13 \text{ V}$		0.1	1.0		0.1	3.0	pV/V
POWER SUPPLY REJECTION RATIO	PSRR	$V_S = \pm 3 \text{ V to } \pm 18 \text{ V}$		1.0	3.0		1.0	5.0	μV/V
LARGE-SIGNAL VOLTAGE GAIN	Avo	$R_L \ge 2 \ k\Omega$	2000	6000		1000	4000		V/mV
		$V_0 = \pm 10 \text{ V}$							
OUTPUT VOLTAGE SWING	Vo	$R_L \ge 2 \ k\Omega$	±12	±13.0	•	±12	±13.0		V
POWER CONSUMPTION	P _d	$V_S = \pm 15 \text{ V, no load}$		60	75		60	75	mW

 $^{^{\}rm 1}$ OP77E: TCV $_{\rm OS}$ is 100% tested on J and Z packages. $^{\rm 2}$ Guaranteed by end-point limits.

WAFER TEST LIMITS

@ V_S = ±15 V, T_A = 25°C, for OP77NBC devices, unless otherwise noted.

Table 3.

Parameter	Symbol	Conditions	OP77NBC Limit	Unit
INPUT OFFSET VOLTAGE	Vos		40	μV max
INPUT OFFSET CURRENT	los		2.0	nA max
INPUT BIAS CURRENT	I _B		±2	nA max
INPUT RESISTANCE				
Differential Mode	R _{IN}		26	MΩ min
INPUT VOLTAGE RANGE	IVR		±13	V min
COMMON-MODE REJECTION RATIO	CMRR	$V_{CM} = \pm 13 \text{ V}$	1	μV/V max
POWER SUPPLY REJECTION RATIO	PSRR	$V_S = \pm 3 \text{ V to } \pm 18 \text{ V}$	3	μV/V max
OUTPUT VOLTAGE SWING	Vo	$R_L = 10 \text{ k}\Omega$	±13.5	V min
		$R_L = 2 k\Omega$	±12.5	
		$R_L = 1 \text{ k}\Omega$	±12.0	
LARGE-SIGNAL VOLTAGE GAIN	A _{VO}	$R_L = 2 k\Omega$	2000	V/mV min
		$V_0 = \pm 10 \text{ V}$		
DIFFERENTIAL INPUT VOLTAGE			±30	V max
POWER CONSUMPTION	P _d	$V_O = 0 V$	60	mW max

TYPICAL ELECTRICAL CHARACTERISTICS

@ $V_S = \pm 15$ V, $T_A = 25$ °C, unless otherwise noted.

Table 4.

Parameter	Symbol	Conditions	OP77NBC Limit	Unit
AVERAGE INPUT OFFSET VOLTAGE DRIFT	TCVos	$R_S = 50 \Omega$	0.1	μV/°C
NULLED INPUT OFFSET VOLTAGE DRIFT	TCV _{OSn}	$R_S = 50 \Omega$, $R_P = 20 k\Omega$	0.1	μV/°C
AVERAGE INPUT OFFSET CURRENT DRIFT	TClos		0.5	pA/°C
SLEW RATE	SR	$R_L \ge 2 \ k\Omega$	0.3	V/µs
BANDWIDTH	BW	A _{VCL} + 1	0.6	MHz

ABSOLUTE MAXIMUM RATINGS

Table 5.

Parameter ¹	Detin a
Parameter .	Rating
Supply Voltage	±22 V
Differential Input Voltage	±30 V
Input Voltage ²	±22 V
Output Short-Circuit Duration	Indefinite
Storage Temperature Range	−65°C to +150°C
Operating Temperature Range	−25°C to +85°C
Junction Temperature (T _J)	−65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C

¹Absolute Maximum Ratings apply to both dice and packaged parts, unless otherwise noted.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

Table 6.

Package Type	θ_{JA}^1	θις	Unit
8-Pin TO-99 H-08 (J Suffix)	150	18	°C/W
8-Lead Hermetic CERDIP Q-8 (Z Suffix)	148	16	°C/W

 $^{^{1}\}theta_{JA}$ is specified for worst-case mounting conditions, i.e., θ_{JA} is specified for a device in socket for the TO-99 and CERDIP packages.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

 $^{^2\}text{For}$ supply voltages less than ± 22 V, the absolute maximum input voltage is equal to the supply voltage.

TYPICAL PERFORMANCE CHARACTERISTICS

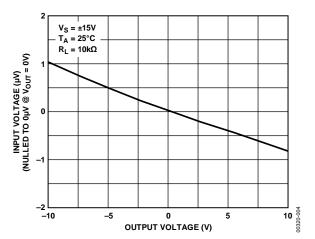


Figure 3. Gain Linearity (Input Voltage vs. Output Voltage)

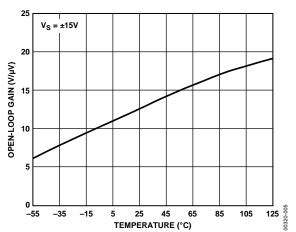


Figure 4. Open-Loop Gain vs. Temperature

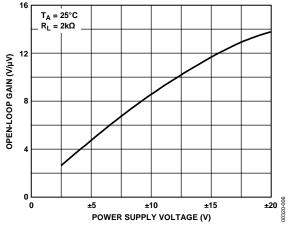


Figure 5. Open-Loop Gain vs. Power Supply Voltage

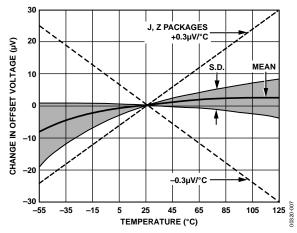


Figure 6. Untrimmed Offset Voltage vs. Temperature

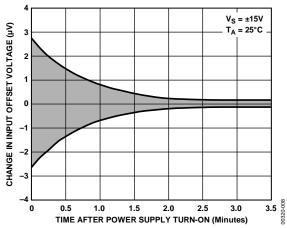


Figure 7. Warm-Up Drift

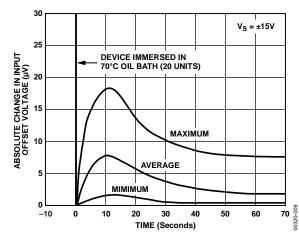


Figure 8. Offset Voltage Change Due to Thermal Shock

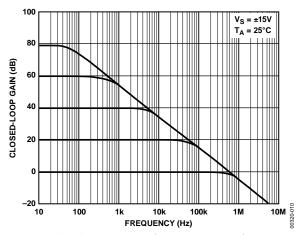


Figure 9. Closed-Loop Response for Various Gain Configurations

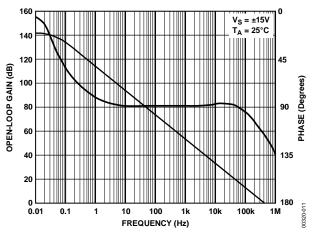


Figure 10. Open-Loop Gain/Phase Response

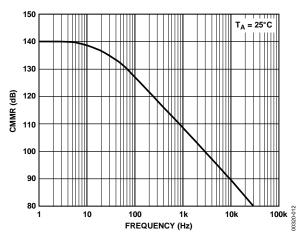


Figure 11. CMRR vs. Frequency

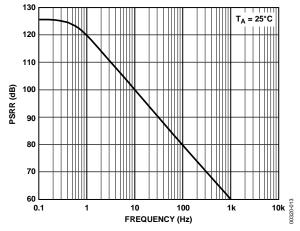


Figure 12. PSRR vs. Frequency

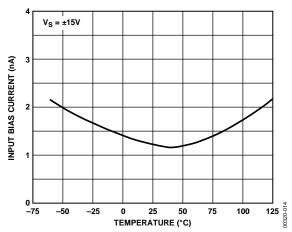


Figure 13. Input Bias Current vs. Temperature

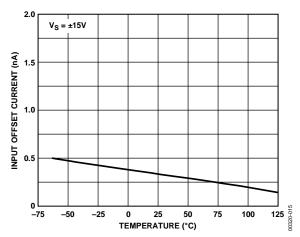


Figure 14. Input Offset Current vs. Temperature

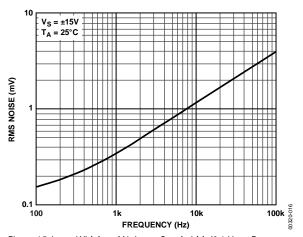


Figure 15. Input Wideband Noise vs. Bandwidth (0.1 Hz to Frequency Indicated)

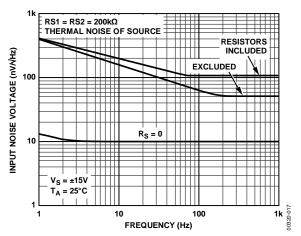


Figure 16. Total Input Noise Voltage vs. Frequency

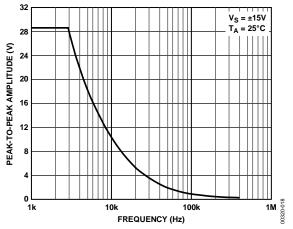


Figure 17. Maximum Output Swing vs. Frequency

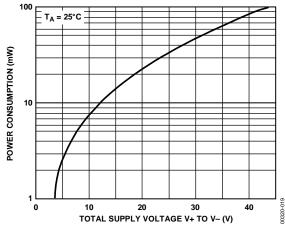


Figure 18. Power Consumption vs. Power Supply

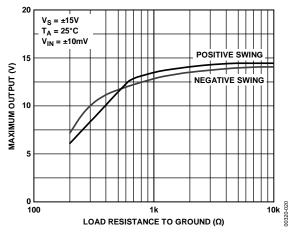


Figure 19. Maximum Output Voltage vs. Load Resistance

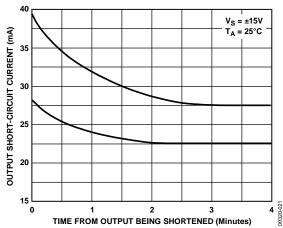


Figure 20. Output Short-Circuit Current vs. Time

TEST CIRCUITS

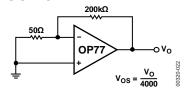


Figure 21. Typical Offset Voltage Test Circuit

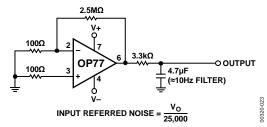


Figure 22. Typical Low-Frequency Noise Test Circuit

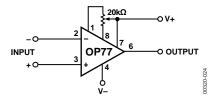


Figure 23. Optional Offset Nulling Circuit

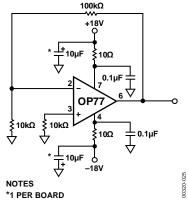
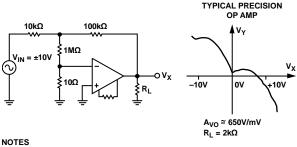


Figure 24. Burn-In Circuit



- 1. GAIN NOT CONSISTANT. CAUSES NONLINEAR ERRORS.
- 2. A_{VO} SPEC IS ONLY PART OF THE SOLUTION.
- 3. CHECK SPECIFICATION TABLE 1 AND TABLE 2 FOR PERFORMANCE.

Figure 25. Open-Loop Gain Linearity

Actual open-loop voltage gain can vary greatly at various output voltages. All automated testers use endpoint testing and therefore only show the average gain. This causes errors in high closed-loop gain circuits. Because this is difficult for manufacturers to test, users should make their own evaluations. This simple test circuit makes it easy. An ideal op amp would show a horizontal scope trace.

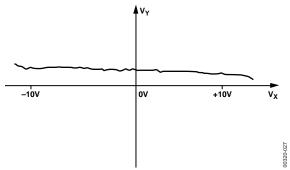


Figure 26. Output Gain Linearity Trace

This is the output gain linearity trace for the new OP77. The output trace is virtually horizontal at all points, assuring extremely high gain accuracy. The average open-loop gain is truly impressive—approximately 10,000,000.

APPLICATIONS

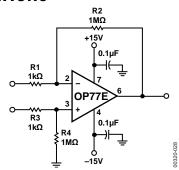


Figure 27. Precision High-Gain Differential Amplifier

The high gain, gain linearity, CMRR, and low TCV_{OS} of the OP77 make it possible to obtain performance not previously available in single-stage, very high-gain amplifier applications.

For best CMR, $\frac{R1}{R2}$ must equal $\frac{R3}{R4}$. In this example, with a 10 mV differential signal, the maximum errors are as listed in Table 7.

Table 7. Maximum Errors

Туре	Amount
Common-Mode Voltage	0.01%/V
Gain Linearity, Worst Case	0.02%
TCVos	0.003%/°C
TClos	0.008%/°C

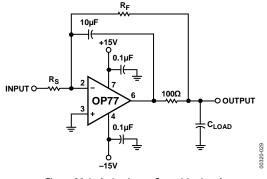


Figure 28. Isolating Large Capacitive Loads

This circuit reduces maximum slew rate but allows driving capacitive loads of any size without instability. Because the boon resistor is inside the feedback loop, its effect on output impedance is reduced to insignificance by the high open-loop gain of the OP77.

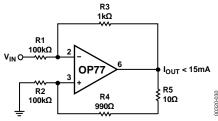


Figure 29. Basic Current Source

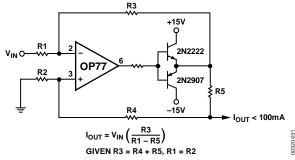


Figure 30. 100 mA Current Source

These current sources can supply both positive and negative current into a grounded load.

Note that

$$Z_{O} = \frac{R5\left(\frac{R4}{R2} + 1\right)}{\frac{R5 + R4}{R2} \frac{R3}{R1}}$$

And that for
$$Z_0$$
 to be infinite $\frac{R5 + R4}{R2}$ must = $\frac{R3}{R1}$

PRECISION CURRENT SINKS

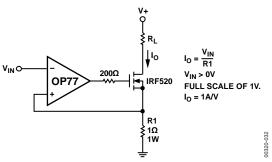


Figure 31. Positive Current Sink

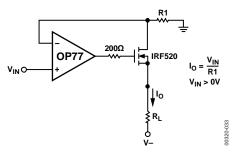


Figure 32. Positive Current Source

The simple high-current sinks, shown Figure 31 and Figure 32, require the load to float between the power supply and the sink.

In these circuits, the high gain, high CMRR, and low TCV_{OS} of the OP77 ensure high accuracy.

The high gain and low TCV_{OS} ensure accurate operation with inputs from microvolts to volts. In Figure 33, the signal always appears as a common-mode signal to the op amps. The OP77EZ CMRR of 1 μ V/V ensures errors of less than 2 ppm.

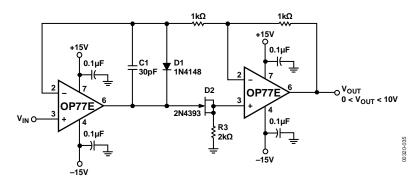


Figure 33. Precision Absolute Value Amplifier

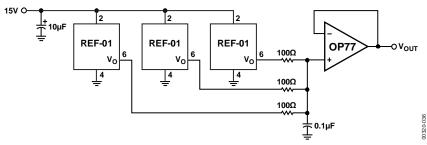


Figure 34. Low Noise Precision Reference

Figure 34 relies upon low TCV_{OS} of the OP77 and noise combined with very high CMRR to provide precision buffering of the averaged REF-01 voltage outputs.

In Figure 35, C_H must be of polystyrene, Teflon*, or polyethylene to minimize dielectric absorption and leakage. The droop rate is determined by the size of C_H and the bias current of the AD820.

*Teflon is a registered trademark of the Dupont Company

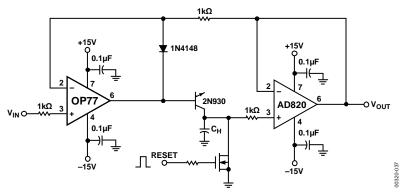


Figure 35. Precision Positive Peak Detector

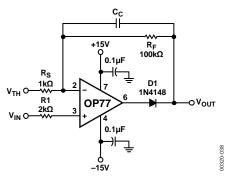


Figure 36. Precision Threshold Detector/Amplifier

When $V_{\rm IN}$ < $V_{\rm TH}$, amplifier output swings negative, reversing the biasing diode D1. $V_{\rm O}$ = $V_{\rm TH}$ if R_{L} = ∞ when $V_{\rm IN}$ > $V_{\rm TH}$, the loop closes,

$$V_O = V_{TH} + \left(V_{IN} - V_{TH}\right) \left(1 + \frac{R_F}{R_S}\right)$$

 $C_{\mbox{\scriptsize C}}$ is selected to smooth the response of the loop.

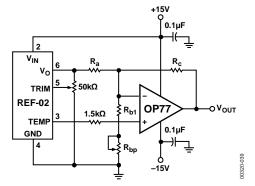
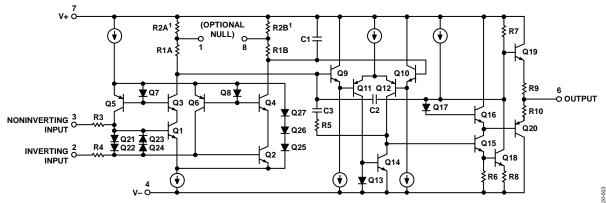


Figure 37. Precision Temperature Sensor

Table 8. Resistor Values

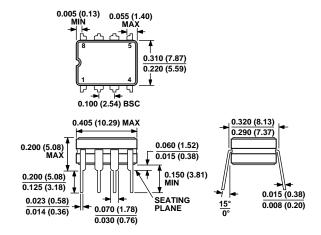
TCV _{OUT} Slope (S)	10 mV/°C	100 mV/°C	10 mV/°F
Temperature Range	−55°C to +125°C	−55°C to +125°C	−67°F to +257°C
Output Voltage Range	-0.55 V to +1.25 V	−5.5 V to +12.5V	-0.67 V to +2.57V
Zero-Scale	0 V @ 0°C	0 V @ 0°C	0 V @ 0°F
R _a (±1% Resistor)	9.09 kΩ	15 kΩ	7.5 kΩ
R _{b1} (±1% Resistor)	1.5 kΩ	1.82 kΩ	1.21 kΩ
R _{bp} (Potentiometer)	200 Ω	500 Ω	200 Ω
R _c (±1% Resistor)	5.11 kΩ	84.5 kΩ	8.25 kΩ



¹R2A AND R2B ARE ELECTRONICALLY ADJUSTED ON CHIP AT FACTORY.

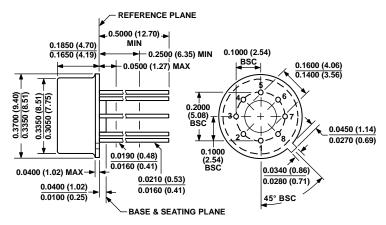
Figure 38. Simplified Schematic

OUTLINE DIMENSIONS



CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 39. 8-Lead Ceramic Dual In-Line Package [CERDIP] (Q-8) Dimensions shown in inches and (millimeters)



COMPLIANT TO JEDEC STANDARDS MO-002-AK
CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 40. 8-Pin Metal Header [TO-99] (H-08)

Dimensions shown in inches and (millimeters)

OP77

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
OP77FJ	−25°C to +85°C	8-Pin Metal Header [TO-99]	H-08 (J Suffix)
OP77FJZ	−25°C to +85°C	8-Pin Metal Header [TO-99]	H-08 (J Suffix)
OP77EZ	−25°C to +85°C	8-Lead Ceramic Dual In-Line Package [CERDIP]	Q-8 (Z Suffix)
OP77FZ	−25°C to +85°C	8-Lead Ceramic Dual In-Line Package [CERDIP]	Q-8 (Z Suffix)
OP77NBC		Die	

¹ Z = RoHS Compliant Part.